

ANTREX Electronics

Electronic Components Sourcing Information

Product Reference Information

Part Number: AIMZH120R040M1TXKSA1

Manufacturer: Infineon Technologies

Package: Please confirm with sales

Availability: Please confirm with sales

Product Page:

<https://antrexco.com/product/details/infineon-technologies/aimzh120r040m1txksa1.html>

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Contact Information

Email: info@antrexco.com

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Supplier verification and packaging condition review

CoC / RoHS / REACH documents available on request

Secure sourcing support for OEM / EMS projects

Note:

This PDF includes an ANTREX product reference cover page.

The original manufacturer datasheet follows from the next page.

Final datasheet

CoolSiC™ 1200 V SiC Trench MOSFET

Features

- $V_{DS} = 1200\text{ V}$ at $T_{vj} = -55...175^{\circ}\text{C}$
- $I_{DDC} = 55\text{ A}$ at $T_C = 25^{\circ}\text{C}$
- New performance-optimized chip technology (Gen1p) with improved $R_{DS(on)}$ * A FOM
- Increased recommended turn-on voltage ($V_{GS(on)} = 20\text{ V}$) for lower $R_{DS(on)}$
- Best-in-class switching energy for lower switching losses and reduced cooling efforts
- Lowest device capacitances for higher switching speeds and higher power density
- A combination of low C_{rss}/C_{iss} ratio and high $V_{GS(th)}$ to avoid parasitic turn-on and enable unipolar gate driving
- Reduced total gate charge Q_{Gtot} for lower driving power and losses
- .XT die attach technology for best-in-class thermal performance
- Sense pin for optimized switching performance
- Minimum creepage distance of 7.07 mm to fit HV requirements

Potential applications

- On-board charger
- DC/DC converter
- Auxiliary drives

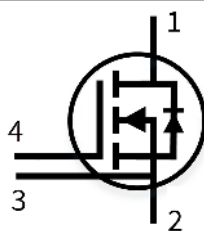
Product validation

- Qualified for Automotive Applications. Product Validation according to AEC-Q100/101

Description

Pin definition:

- 1 – drain
- 2 – source
- 3 – Kelvin sense contact
- 4 – gate



Type	Package	Marking
AIMZH120R040M1T	PG-TO247-4-U03	A12M1T040



Table of contents

	Description	1
	Features	1
	Potential applications	1
	Product validation	1
	Table of contents	2
1	Package	3
2	MOSFET	3
3	Body diode (MOSFET)	5
4	Characteristics diagrams	7
5	Package outlines	13
6	Testing conditions	14
	Revision history	15
	Disclaimer	16

1 Package

1 Package

Table 1 Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Storage temperature	T_{stg}		-55		150	°C
Soldering temperature	T_{sold}				260	°C
MOSFET/body diode thermal resistance, junction-case ¹⁾	$R_{th(j-c)}$			0.45	0.56	K/W

1) Not subject to production test. Parameter verified by design / characterization

2 MOSFET

Table 2 Maximum rated values

Parameter	Symbol	Note or test condition		Values	Unit
Drain-source voltage ¹⁾	V_{DSS}	$T_{vj} = -55...175\text{ °C}$		1200	V
Continuous DC drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$ ²⁾	I_{DDC}	$V_{GS} = 20\text{ V}$	$T_c = 25\text{ °C}$	55	A
			$T_c = 100\text{ °C}$	39	
Peak drain current, t_p limited by $T_{vj(max)}$ ²⁾	I_{DM}	$V_{GS} = 20\text{ V}$		140	A
Gate-source voltage, max. transient voltage ³⁾	V_{GS}	$t_p \leq 0.5\text{ }\mu\text{s}$, $D < 0.01$		-10...25	V
Gate-source voltage, max. static voltage ³⁾	V_{GS}			-5...23	V
Avalanche energy, single pulse	E_{AS}	$I_D = 15\text{ A}$, $V_{DD} = 50\text{ V}$, $L = 2.41\text{ mH}$		269	mJ
Power dissipation, limited by $T_{vj(max)}$ ²⁾	P_{tot}		$T_c = 25\text{ °C}$	268	W
			$T_c = 100\text{ °C}$	134	

1) Tested at $T_{vj}=25\text{ °C}$, verified by design/characterization over full temperature range

2) Not subject to production test. Parameter verified by design / characterization

3) **Important note:** The selection of positive and negative gate-source voltages impacts the long-term behavior of the device. The design guidelines described in Application Note AN2018-09 must be considered to ensure sound operation of the device over the planned lifetime.

Table 3 Recommended values

Parameter	Symbol	Note or test condition	Values	Unit
Recommended turn-on gate voltage	$V_{GS(on)}$		20	V
Recommended turn-off gate voltage	$V_{GS(off)}$		0	V

Table 4 **Characteristic values**

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source on-state resistance	$R_{DS(on)}$	$I_D = 20 \text{ A}$	$T_{vj} = 25 \text{ °C}$, $V_{GS(on)} = 20 \text{ V}$		40	50	mΩ
			$T_{vj} = 100 \text{ °C}$, $V_{GS(on)} = 20 \text{ V}$		56		
			$T_{vj} = 175 \text{ °C}$, $V_{GS(on)} = 20 \text{ V}$		80		
			$T_{vj} = 25 \text{ °C}$, $V_{GS(on)} = 18 \text{ V}$		44		
Gate-source threshold voltage	$V_{GS(th)}$	$I_D = 6.4 \text{ mA}$, $V_{DS} = V_{GS}$ (tested after 1 ms pulse at $V_{GS} = 20 \text{ V}$)	$T_{vj} = 25 \text{ °C}$	3.7	4.4	5.1	V
			$T_{vj} = 175 \text{ °C}$		3.6		
Zero gate-voltage drain current	I_{DSS}	$V_{DS} = 1200 \text{ V}$, $V_{GS} = 0 \text{ V}$	$T_{vj} = 25 \text{ °C}$		0.3	19	μA
			$T_{vj} = 175 \text{ °C}$		50		
Gate leakage current	I_{GSS}	$V_{DS} = 0 \text{ V}$	$V_{GS} = 25 \text{ V}$			100	nA
			$V_{GS} = -10 \text{ V}$			-100	
Forward transconductance	g_{fs}	$I_D = 20 \text{ A}$, $V_{DS} = 20 \text{ V}$			12.4		S
Short-circuit withstand time ¹⁾	t_{SC}	$V_{DD} \leq 800 \text{ V}$, $V_{DS,peak} < 1200 \text{ V}$, $T_{vj(start)} = 25 \text{ °C}$, $R_{G,ext} = 2 \text{ } \Omega$	$V_{GS(on)} = 20 \text{ V}$		1.5		μs
			$V_{GS(on)} = 18 \text{ V}$		2		
			$V_{GS(on)} = 15 \text{ V}$		2.5		
Internal gate resistance	$R_{G,int}$	$f = 1 \text{ MHz}$, $V_{AC} = 25 \text{ mV}$			3.7		Ω
Input capacitance	C_{iss}	$V_{DS} = 800 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 100 \text{ kHz}$, $V_{AC} = 25 \text{ mV}$			1264		pF
Output capacitance	C_{oss}	$V_{DS} = 800 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 100 \text{ kHz}$, $V_{AC} = 25 \text{ mV}$			63		pF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 800 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 100 \text{ kHz}$, $V_{AC} = 25 \text{ mV}$			3.6		pF
C_{oss} stored energy	E_{oss}	$V_{DS} = 800 \text{ V}$, $V_{GS} = 0 \text{ V}$, $f = 100 \text{ kHz}$, $V_{AC} = 25 \text{ mV}$			26		μJ
Total gate charge	Q_G	$V_{DD} = 800 \text{ V}$, $I_D = 20 \text{ A}$, $V_{GS} = 0/20 \text{ V}$, turn-on pulse			43		nC
Plateau gate charge	$Q_{GS(pl)}$	$V_{DD} = 800 \text{ V}$, $I_D = 20 \text{ A}$, $V_{GS} = 0/20 \text{ V}$, turn-on pulse			12		nC
Gate-drain charge	Q_{GD}	$V_{DD} = 800 \text{ V}$, $I_D = 20 \text{ A}$, $V_{GS} = 0/20 \text{ V}$, turn-on pulse			7		nC
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 800 \text{ V}$, $I_D = 20 \text{ A}$, $V_{GS} = 0/20 \text{ V}$, $R_{GS(on)} = 2 \text{ } \Omega$, $R_{GS(off)} = 2 \text{ } \Omega$, $L_\sigma = 33 \text{ nH}$	$T_{vj} = 25 \text{ °C}$		10		ns
			$T_{vj} = 175 \text{ °C}$		10		

(table continues...)

Table 4 (continued) Characteristic values

Parameter	Symbol	Note or test condition	Values			Unit
			Min.	Typ.	Max.	
Rise time	t_r	$V_{DD} = 800 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 0/20 \text{ V},$ $R_{GS(on)} = 2 \Omega,$ $R_{GS(off)} = 2 \Omega, L_\sigma = 33 \text{ nH}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	8		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}$	10		
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 800 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 0/20 \text{ V},$ $R_{GS(on)} = 2 \Omega,$ $R_{GS(off)} = 2 \Omega, L_\sigma = 33 \text{ nH}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	18		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}$	19		
Fall time	t_f	$V_{DD} = 800 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 0/20 \text{ V},$ $R_{GS(on)} = 2 \Omega,$ $R_{GS(off)} = 2 \Omega, L_\sigma = 33 \text{ nH}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	9		ns
			$T_{vj} = 175 \text{ }^\circ\text{C}$	10		
Turn-on energy	E_{on}	$V_{DD} = 800 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 0/20 \text{ V},$ $R_{GS(on)} = 2 \Omega,$ $R_{GS(off)} = 2 \Omega, L_\sigma = 33 \text{ nH}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	111		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	194		
Turn-off energy	E_{off}	$V_{DD} = 800 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 0/20 \text{ V},$ $R_{GS(on)} = 2 \Omega,$ $R_{GS(off)} = 2 \Omega, L_\sigma = 33 \text{ nH}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	35		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	36		
Total switching energy	E_{tot}	$V_{DD} = 800 \text{ V}, I_D = 20 \text{ A},$ $V_{GS} = 0/20 \text{ V},$ $R_{GS(on)} = 2 \Omega,$ $R_{GS(off)} = 2 \Omega, L_\sigma = 33 \text{ nH}$	$T_{vj} = 25 \text{ }^\circ\text{C}$	146		μJ
			$T_{vj} = 175 \text{ }^\circ\text{C}$	230		
Virtual junction temperature	T_{vj}		-55		175	$^\circ\text{C}$

1) verified by the design/characterization

Note: Dynamic test circuit see Fig. F.
Characteristics at $T_{vj} = 25^\circ\text{C}$, unless otherwise specified.

3 Body diode (MOSFET)

Table 5 Maximum rated values

Parameter	Symbol	Note or test condition	Values	Unit
Drain-source voltage ¹⁾	V_{DSS}	$T_{vj} = -55...175 \text{ }^\circ\text{C}$	1200	V
Continuous reverse drain current for $R_{th(j-c,max)}$, limited by $T_{vj(max)}$ ²⁾	I_{SDC}	$T_c = 25 \text{ }^\circ\text{C}$	45	A
		$T_c = 100 \text{ }^\circ\text{C}$	29	

(table continues...)

Table 5 (continued) Maximum rated values

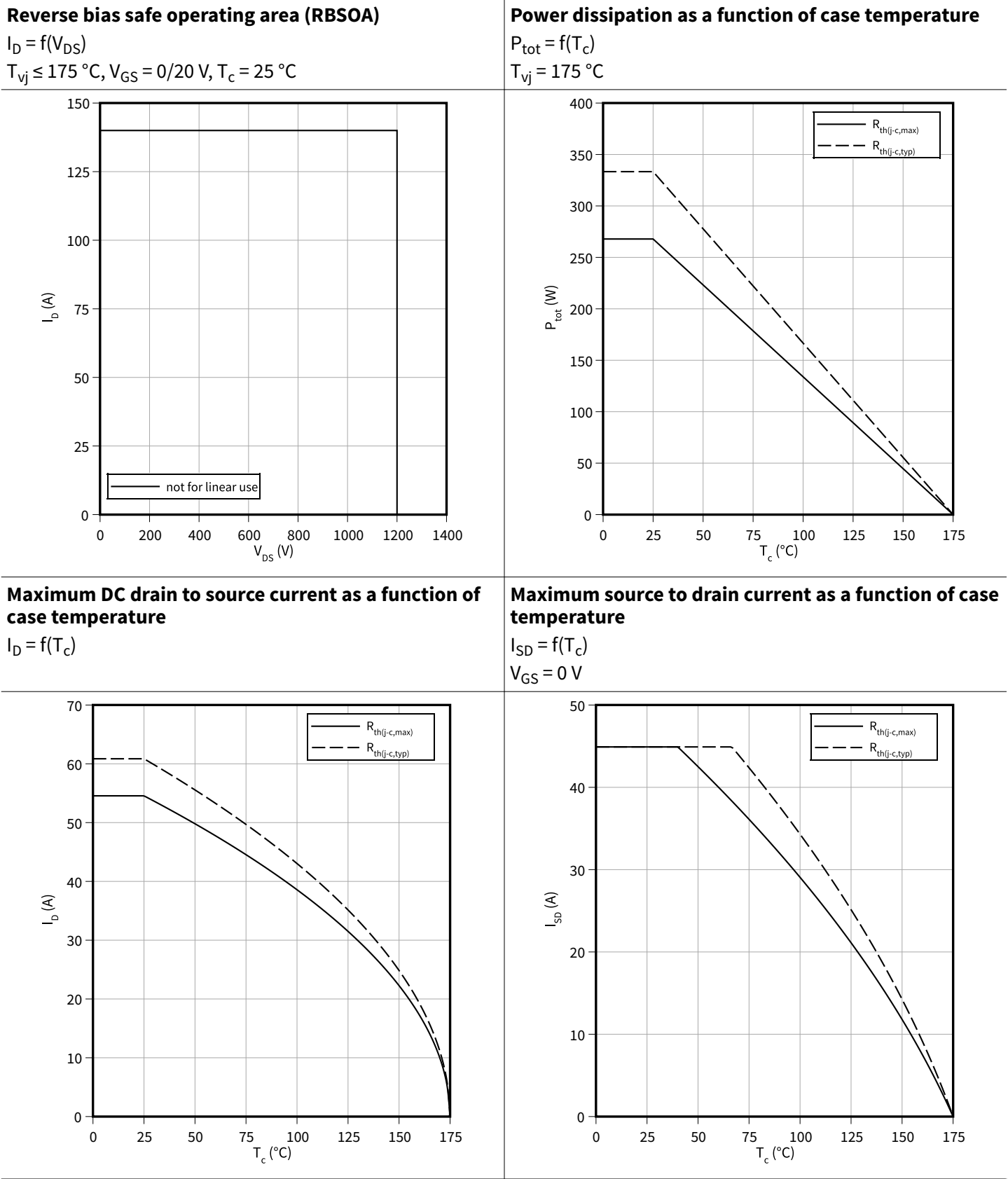
Parameter	Symbol	Note or test condition		Values	Unit
Peak reverse drain current, t_p limited by $T_{vj(max)}$ ²⁾	I_{SM}		$V_{GS} = 0 \text{ V}$	45	A
			$-5 \text{ V} \leq V_{GS} \leq 0 \text{ V}$, $t_p = 0.3 \mu\text{s}$	59	
			$-5 \leq V_{GS} \leq 0 \text{ V}$, $T_{vj} \leq 175^\circ\text{C}$; $t_p \leq 0.3 \text{ ms}$ for accumulated conduction time < 5 s or $t_p \leq 1 \text{ ms}$ for accumulated conduction time < 2.5 s ³⁾	154	

- 1) Tested at $T_{vj}=25^\circ\text{C}$, verified by design/characterization
2) Not subject to production test. Parameter verified by design / characterization
3) Combination of t_p and I_{sm} should not lead to $T_{vj(max)} > 175^\circ\text{C}$

Table 6 Characteristic values

Parameter	Symbol	Note or test condition		Values			Unit
				Min.	Typ.	Max.	
Drain-source reverse voltage	V_{SD}	$I_{SD} = 20 \text{ A}$	$T_{vj} = 25^\circ\text{C}$		3.9	5	V
			$T_{vj} = 100^\circ\text{C}$		3.8		
			$T_{vj} = 175^\circ\text{C}$		3.7		
MOSFET forward recovery charge	Q_{fr}	$V_{DD} = 800 \text{ V}$, $I_{SD} = 20 \text{ A}$, $V_{GS} = 0 \text{ V}$, $-di_{SD}/dt = 2000 \text{ A}/\mu\text{s}$, Q_{fr} includes also Q_C	$T_{vj} = 25^\circ\text{C}$		179		nC
			$T_{vj} = 175^\circ\text{C}$		412		
MOSFET peak forward recovery current	I_{frm}	$V_{DD} = 800 \text{ V}$, $I_{SD} = 20 \text{ A}$, $V_{GS} = 0 \text{ V}$, $-di_{SD}/dt = 2000 \text{ A}/\mu\text{s}$, Q_{fr} includes also Q_C	$T_{vj} = 25^\circ\text{C}$		17		A
			$T_{vj} = 175^\circ\text{C}$		31		
Virtual junction temperature	T_{vj}			-55		175	$^\circ\text{C}$

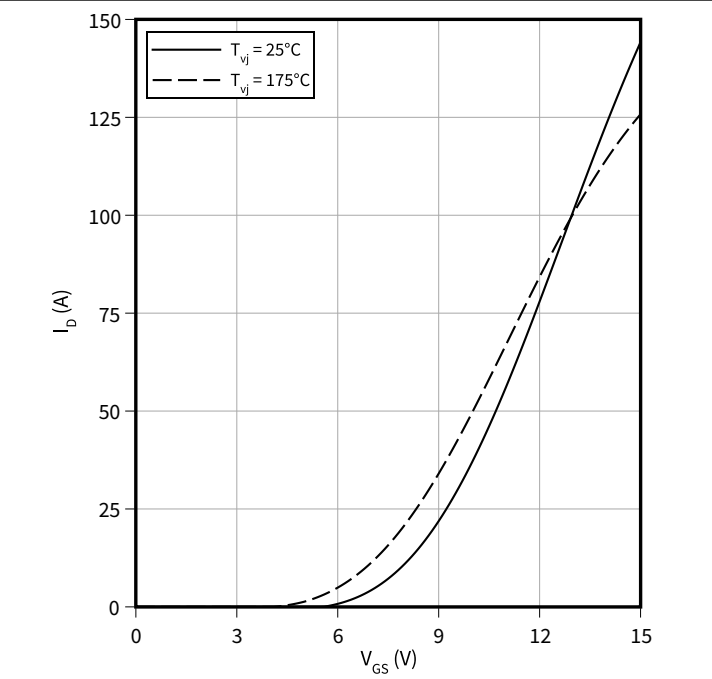
4 Characteristics diagrams



4 Characteristics diagrams

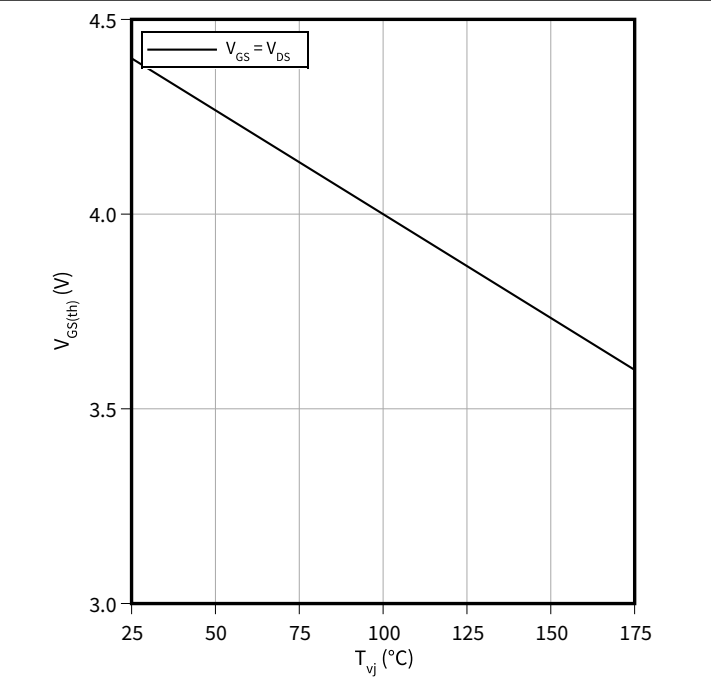
Typical transfer characteristic

$I_D = f(V_{GS})$
 $V_{DS} = 20\text{ V}$, $t_p = 20\text{ }\mu\text{s}$



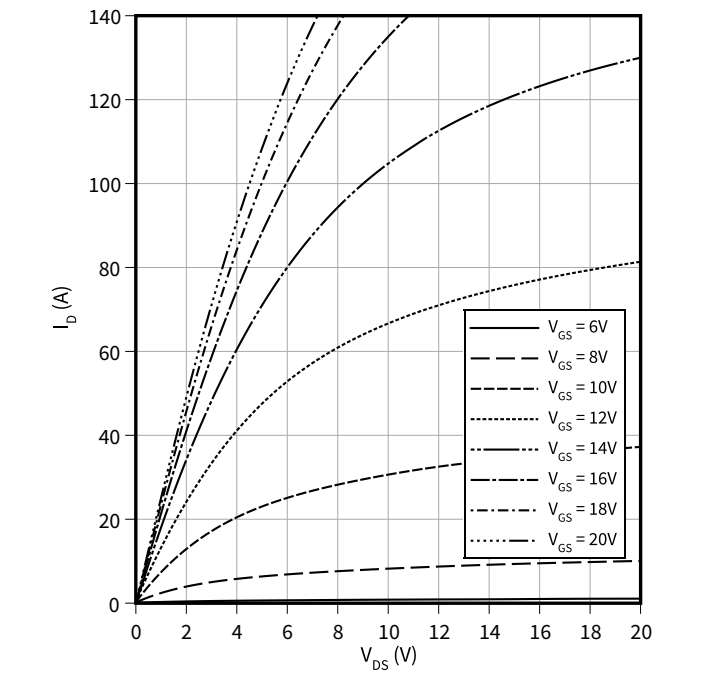
Typical gate-source threshold voltage as a function of junction temperature

$V_{GS(th)} = f(T_{vj})$
 $I_D = 6.4\text{ mA}$



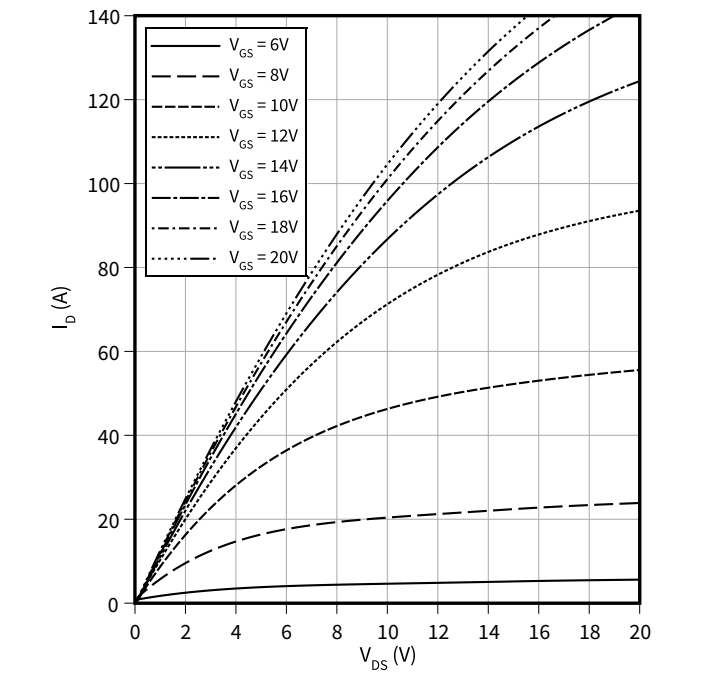
Typical output characteristic, V_{GS} as parameter

$I_D = f(V_{DS})$
 $T_{vj} = 25\text{ }^\circ\text{C}$, $t_p = 20\text{ }\mu\text{s}$



Typical output characteristic, V_{GS} as parameter

$I_D = f(V_{DS})$
 $T_{vj} = 175\text{ }^\circ\text{C}$, $t_p = 20\text{ }\mu\text{s}$

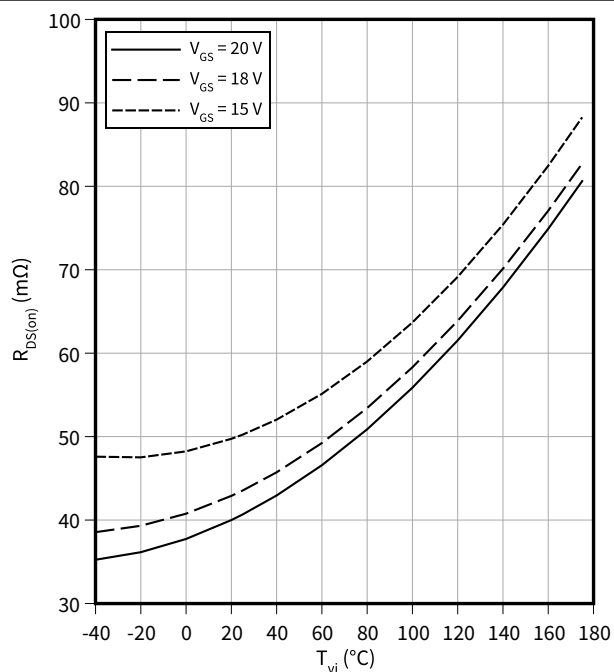


4 Characteristics diagrams

Typical on-state resistance as a function of junction temperature

$$R_{DS(on)} = f(T_{vj})$$

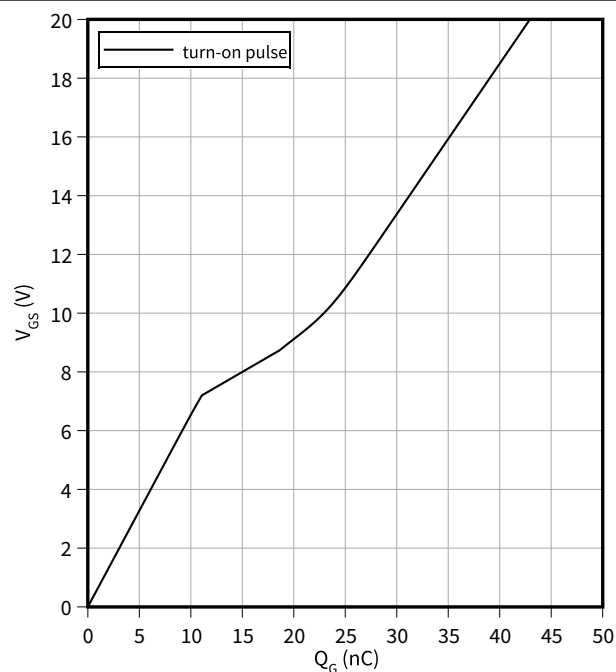
$$I_D = 20 \text{ A}$$



Typical gate charge

$$V_{GS} = f(Q_G)$$

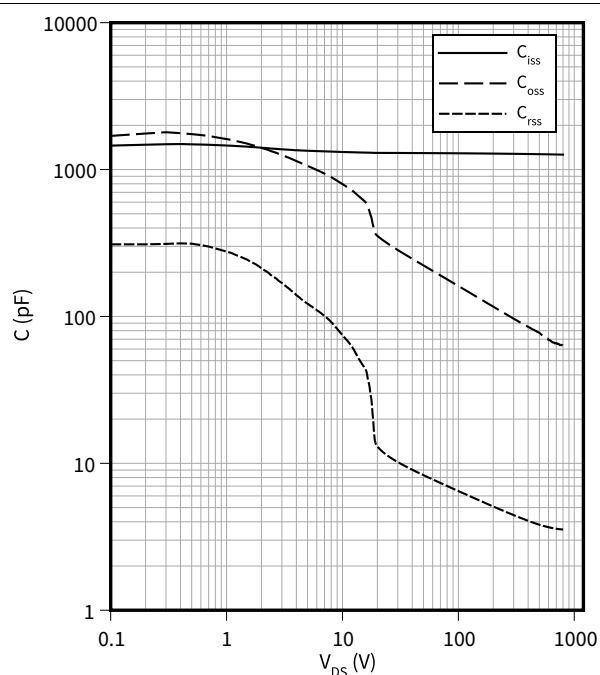
$$I_D = 20 \text{ A}, V_{DS} = 800 \text{ V}$$



Typical capacitance as a function of drain-source voltage

$$C = f(V_{DS})$$

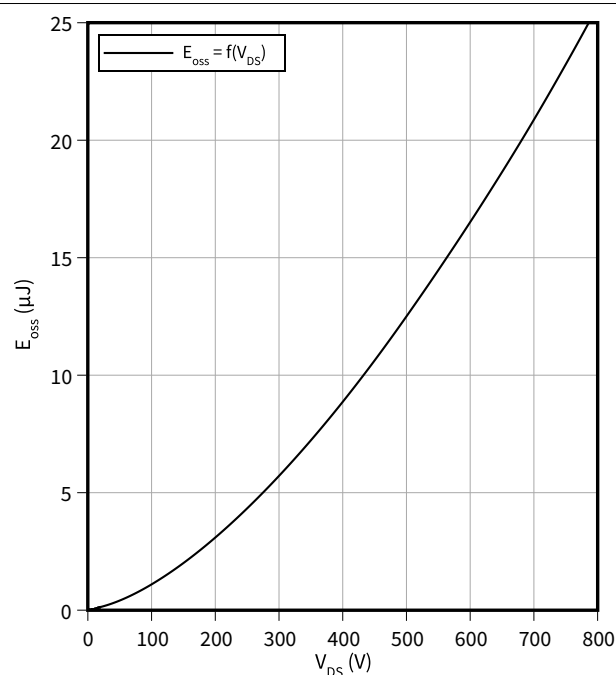
$$f = 100 \text{ kHz}, V_{GS} = 0 \text{ V}$$



Typical C_{OSS} stored energy

$$E_{OSS} = f(V_{DS})$$

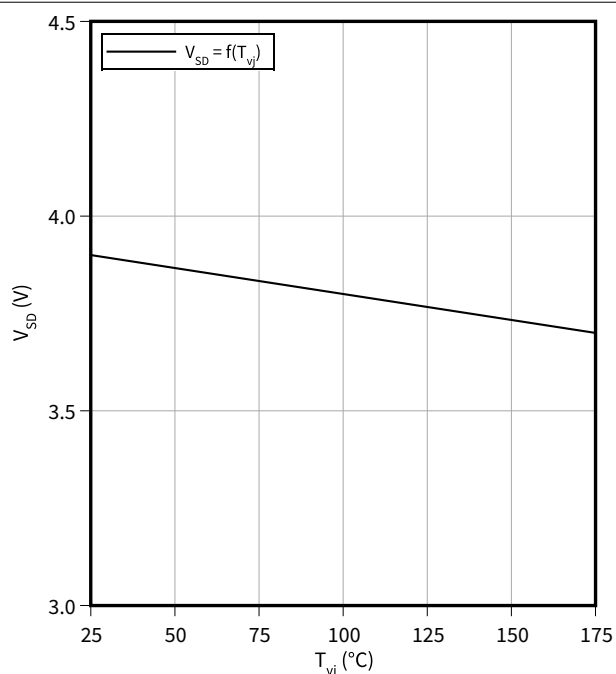
$$f = 100 \text{ kHz}, V_{GS} = 0 \text{ V}$$



4 Characteristics diagrams

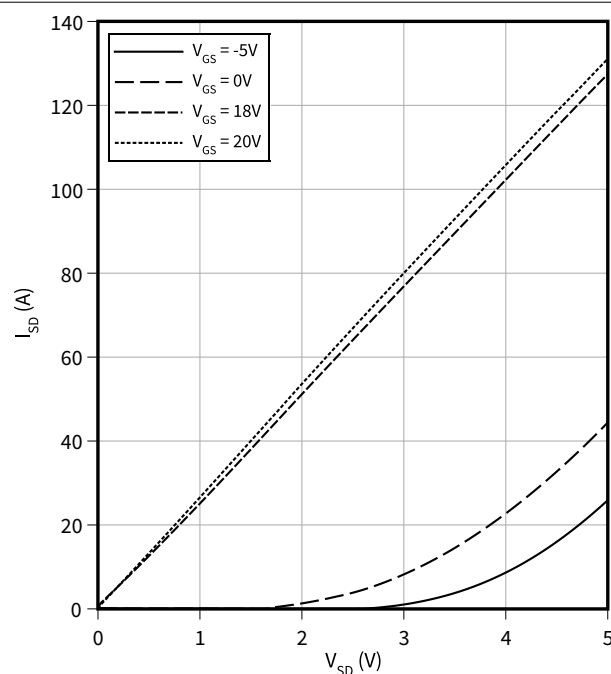
Typical reverse drain voltage as function of junction temperature

$V_{SD} = f(T_{vj})$
 $I_{SD} = 20 \text{ A}$, $V_{GS} = 0 \text{ V}$



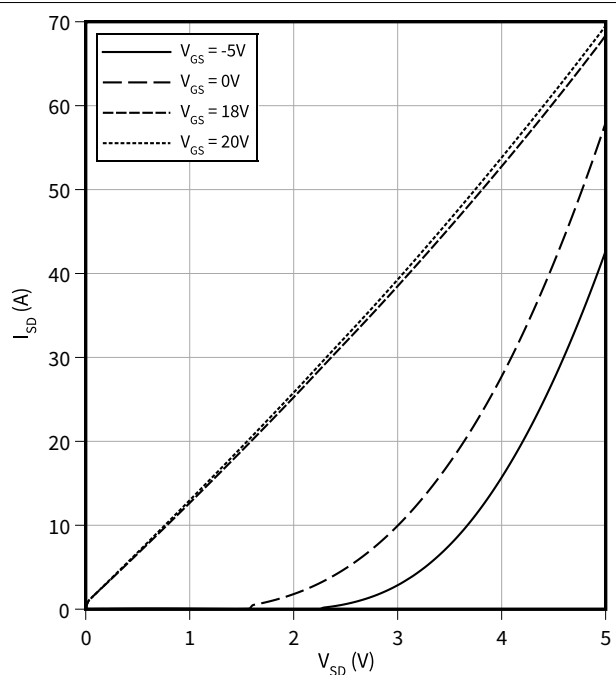
Typical reverse drain current as function of reverse drain voltage, V_{GS} as parameter

$I_{SD} = f(V_{SD})$
 $T_{vj} = 25 \text{ °C}$, $t_p = 20 \text{ } \mu\text{s}$



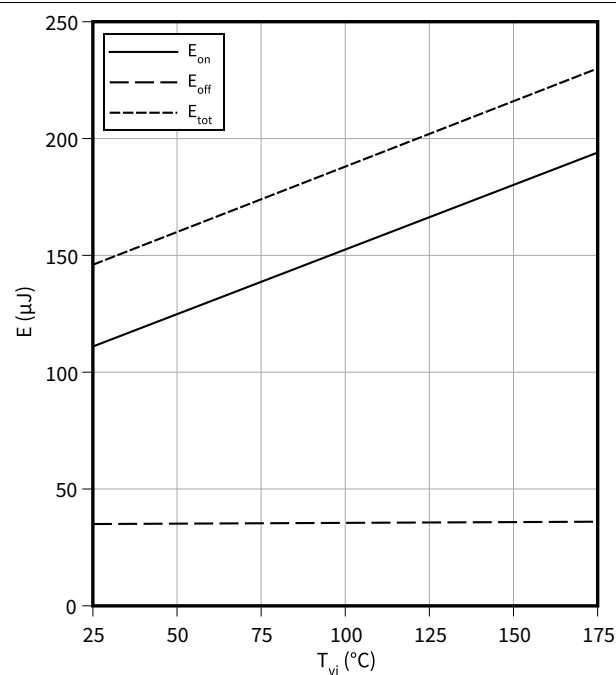
Typical reverse drain current as function of reverse drain voltage, V_{GS} as parameter

$I_{SD} = f(V_{SD})$
 $T_{vj} = 175 \text{ °C}$, $t_p = 20 \text{ } \mu\text{s}$



Typical switching energy as a function of junction temperature, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0 \text{ V}$

$E = f(T_{vj})$
 $V_{GS} = 0/20 \text{ V}$, $I_D = 20 \text{ A}$, $R_{G,ext} = 2 \text{ } \Omega$, $V_{DD} = 800 \text{ V}$

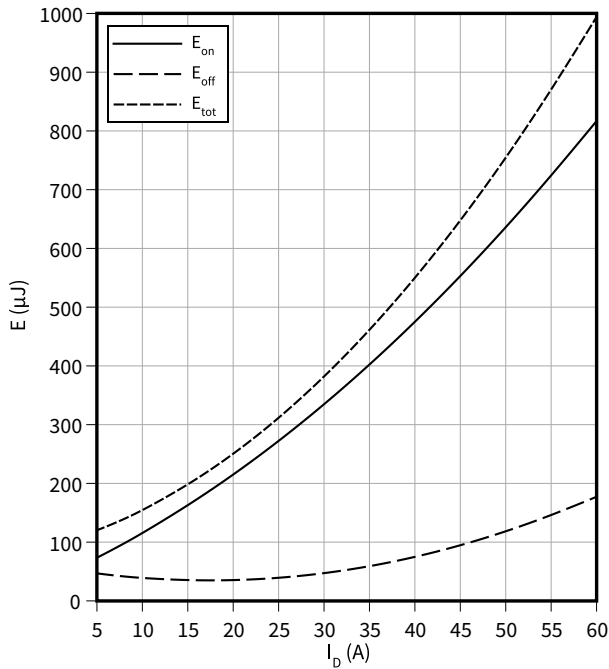


4 Characteristics diagrams

Typical switching energy as a function of drain current, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$E = f(I_D)$$

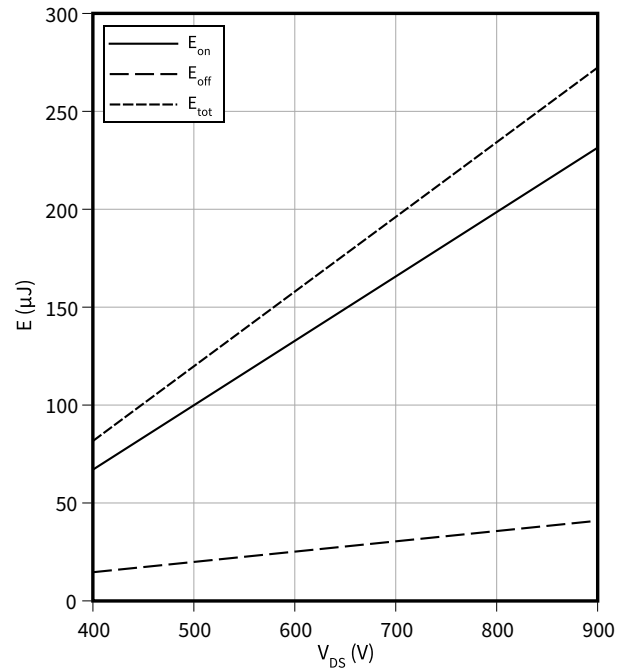
$V_{GS} = 0/20$ V, $T_{vj} = 175$ °C, $R_{G,ext} = 2$ Ω , $V_{DD} = 800$ V



Typical switching energy as a function of drain voltage, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$E = f(V_{DS})$$

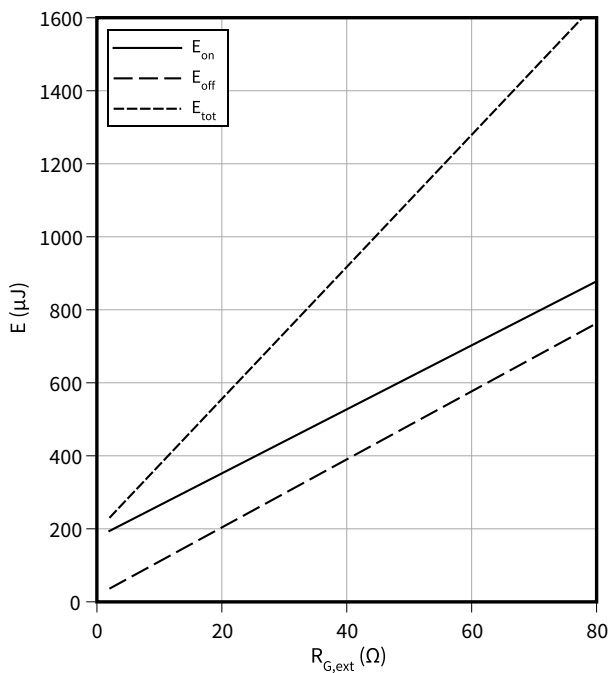
$V_{GS} = 0/20$ V, $I_D = 20$ A, $T_{vj} = 175$ °C, $R_{G,ext} = 2$ Ω



Typical switching energy as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$E = f(R_{G,ext})$$

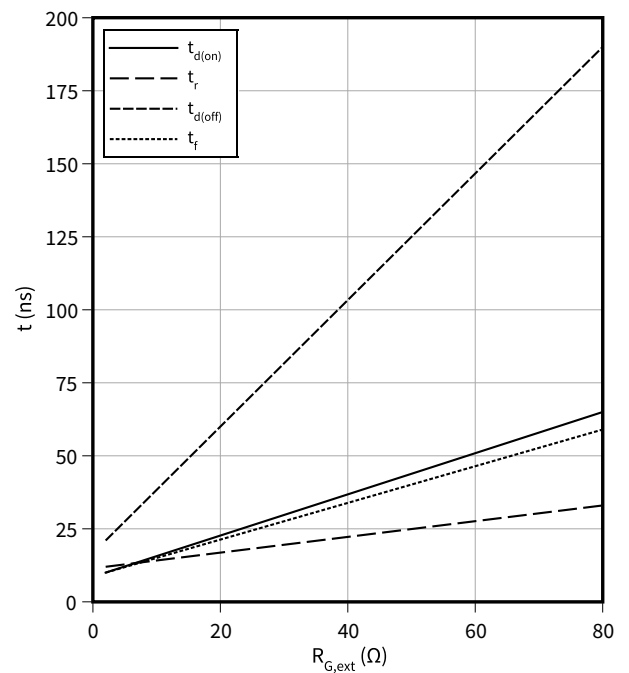
$V_{GS} = 0/20$ V, $I_D = 20$ A, $T_{vj} = 175$ °C, $V_{DD} = 800$ V



Typical switching times as a function of gate resistance, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0$ V

$$t = f(R_{G,ext})$$

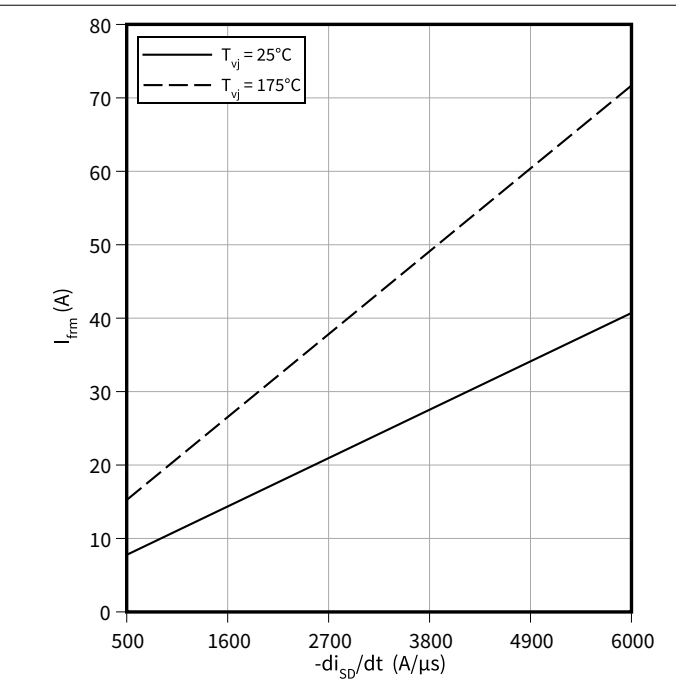
$V_{GS} = 0/20$ V, $I_D = 20$ A, $T_{vj} = 175$ °C, $V_{DD} = 800$ V



4 Characteristics diagrams

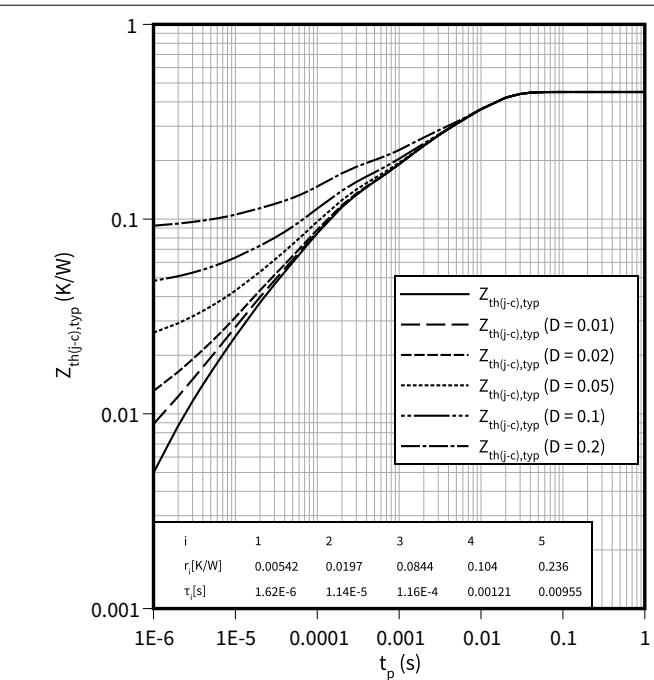
Typical reverse recovery current as a function of reverse drain current slope, test circuit in Fig. F, 2nd device own body diode: $V_{GS} = 0\text{ V}$

$I_{frm} = f(-di_{SD}/dt)$
 $V_{GS} = 0/20\text{ V}, I_{SD} = 20\text{ A}, V_{DD} = 800\text{ V}$



Typ. transient thermal impedance (MOSFET/diode)

$Z_{th(j-c),typ} = f(t_p)$
 $D = t_p/T$



5 Package outlines

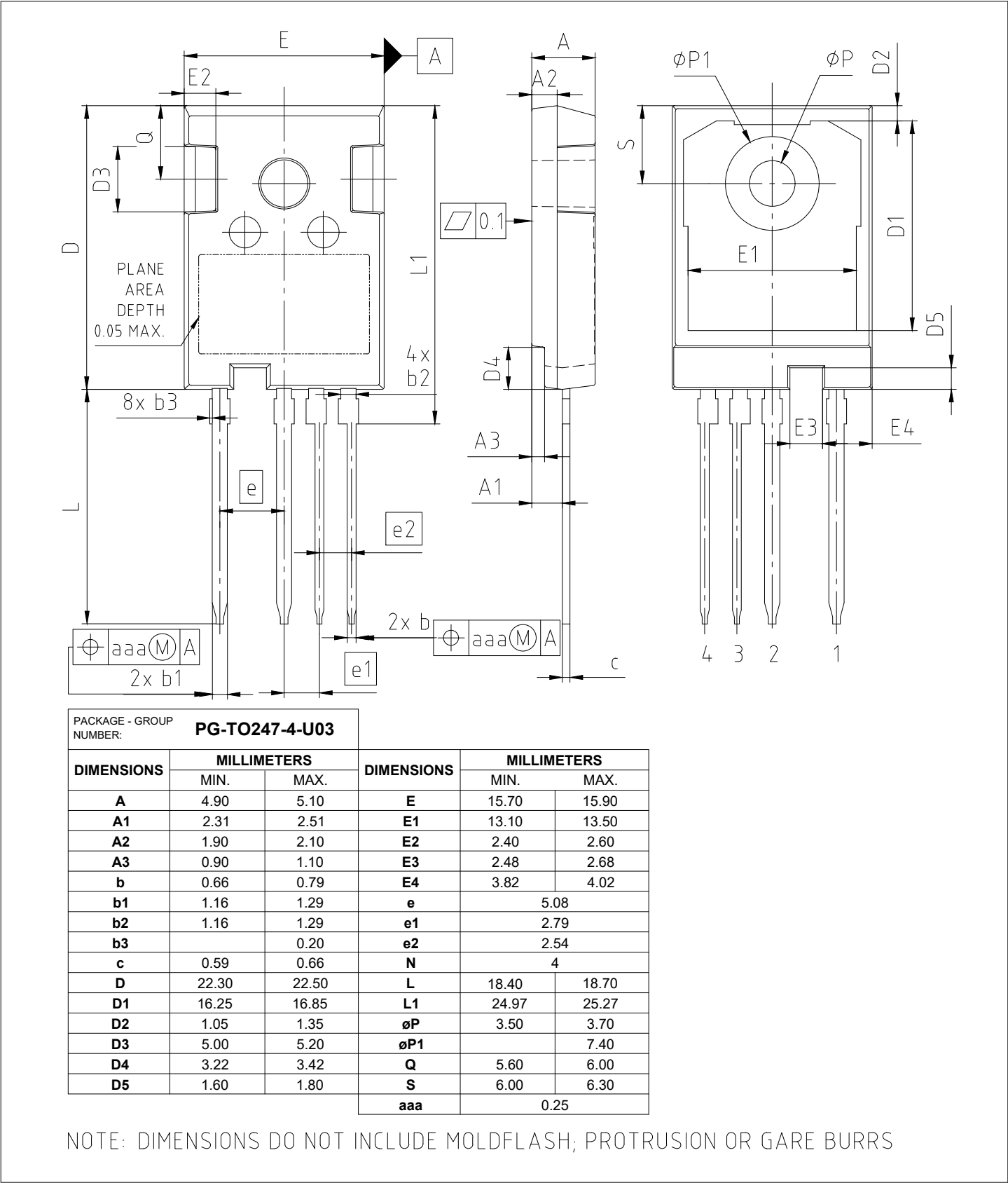


Figure 1

6 Testing conditions

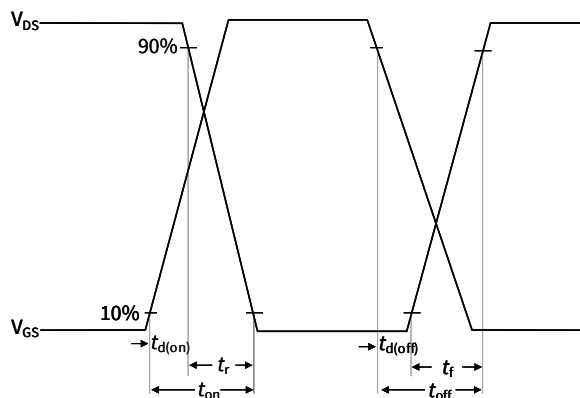


Figure A. Definition of switching times

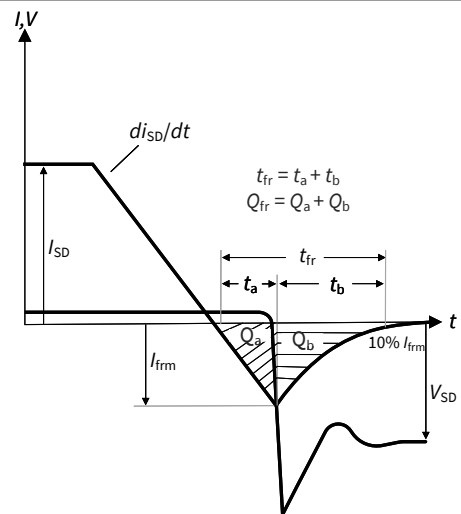


Figure B. Definition of body diode switching characteristics

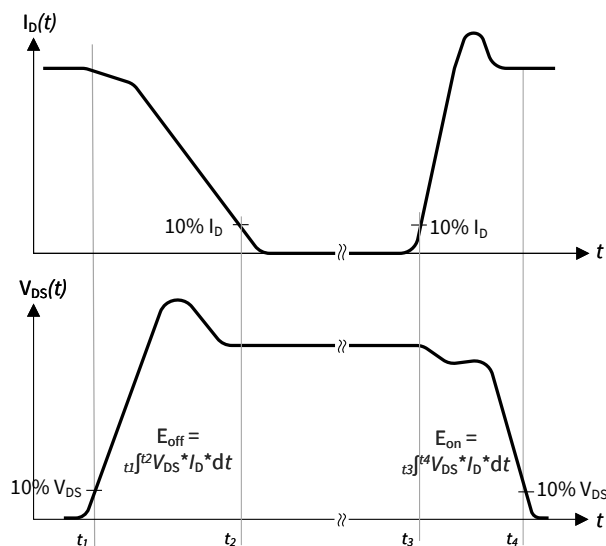


Figure C. Definition of switching losses

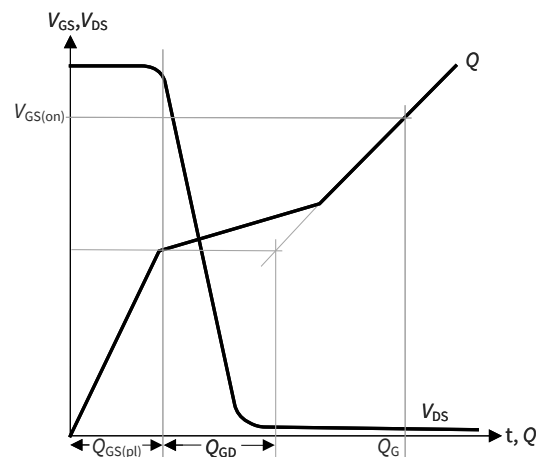


Figure D. Definition of QGD

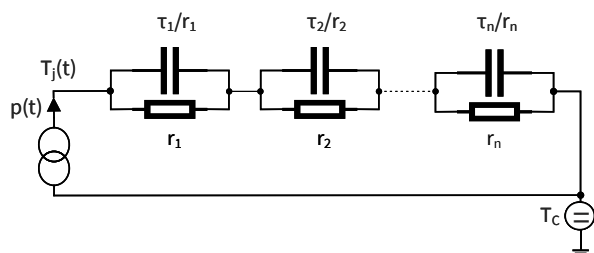


Figure E. Thermal equivalent circuit

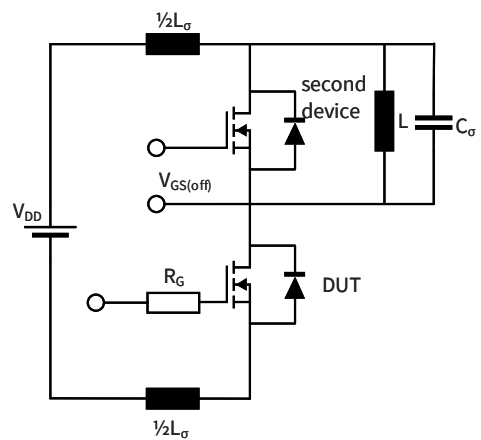


Figure F. Dynamic test circuit

Parasitic inductance L_{σ} ,
Parasitic capacitor C_{σ} ,

Figure 2

Revision history

Document revision	Date of release	Description of changes
0.10	2022-04-19	Target datasheet
0.20	2023-07-31	Preliminary datasheet
0.30	2023-08-03	Correction of inductance unit (p. 3) Correction of diagram template E(Id)
1.00	2023-11-29	Final datasheet
1.10	2025-08-28	Updated table values: g_{fs} , E_{oss} , L_{σ} for switching parameters, $t_{d(on)}$, t_r , $t_{d(off)}$, t_f , E_{on} , E_{off} , E_{tot} , I_{SDC} , Q_{fr} , I_{frm} , condition d_{isd}/dt for Q_{fr} and I_{frm} Added values: creepage distance value on p.1, I_{sm} values for limited t_p Updated graphs: $I_{DS} = f(V_{DS})$, $R_{on}(T_{vj})$, $I_{DS}(V_{GS})$, $I_{SD} = f(V_{SD})$, $E = f(T_{vj})$, $E = f(R_{G,ext})$, $E = f(I_D)$, $t_{sw} = f(R_{G,ext})$, $Z_{th(j-c)} = f(t_p)$ Added graphs: $E_{sw} = f(V_{DS})$, $I_{frm} = f(di/dt)$ No change to the product, new/added values are based on additional assessments

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